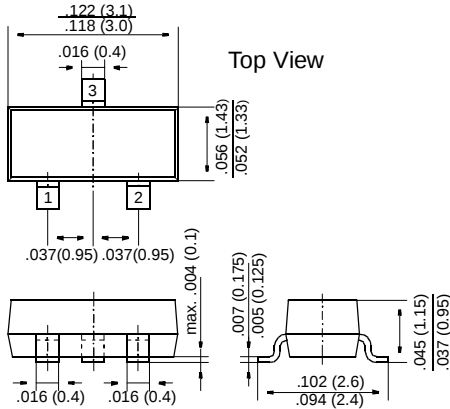


BC856 THRU BC859

Small Signal Transistors (PNP)

SOT-23



Dimensions in inches and (millimeters)

Pin configuration

1 = Base, 2 = Emitter, 3 = Collector.

FEATURES

- ◆ PNP Silicon Epitaxial Planar Transistors for switching and AF amplifier applications.
- ◆ Especially suited for automatic insertion in thick- and thin-film circuits.
- ◆ These transistors are subdivided into three groups A, B and C according to their current gain. The type BC856 is available in groups A and B, however, the types BC857, BC858 and BC859 can be supplied in all three groups. The BC859 is a low noise type.
- ◆ As complementary types, the NPN transistors BC846 ... BC849 are recommended.



MECHANICAL DATA

Case: SOT-23 Plastic Package

Weight: approx. 0.008 g

Marking code

Type	Marking	Type	Marking
BC856A B	3A 3B	BC859A B	4A 4B
BC857A B	3E 3F	C	4C
C	3G		
BC858A	3J		
B	3K		
C	3L		

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Collector-Base Voltage	BC856 BC857 BC858, BC859	$-V_{CB0}$ $-V_{CB0}$ $-V_{CB0}$	V V V
Collector-Emitter Voltage	BC856 BC857 BC858, BC859	$-V_{CES}$ $-V_{CES}$ $-V_{CES}$	V V V
Collector-Emitter Voltage	BC856 BC857 BC858, BC859	$-V_{CEO}$ $-V_{CEO}$ $-V_{CEO}$	V V V
Emitter-Base Voltage		$-V_{EBO}$	V
Collector Current		$-I_C$	mA
Peak Collector Current		$-I_{CM}$	mA
Peak Base Current		$-I_{BM}$	mA
Peak Emitter Current		I_{EM}	mA
Power Dissipation at $T_{SB} = 50\text{ °C}$		P_{tot}	mW
Junction Temperature		T_j	°C
Storage Temperature Range		T_S	°C

BC856 THRU BC859

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Typ.	Max.	Unit
h-Parameters at $-V_{CE} = 5\text{ V}$, $-I_C = 2\text{ mA}$, $f = 1\text{ kHz}$					
Current Gain	Current Gain Group A h_{fe}	—	220	—	—
	B h_{fe}	—	330	—	—
	C h_{fe}	—	600	—	—
Input Impedance	Current Gain Group A h_{ie}	1.6	2.7	4.5	$k\Omega$
	B h_{ie}	3.2	4.5	8.5	$k\Omega$
	C h_{ie}	6	8.7	15	$k\Omega$
Output Admittance	Current Gain Group A h_{oe}	—	18	30	μS
	B h_{oe}	—	30	60	μS
	C h_{oe}	—	60	110	μS
Reverse Voltage Transfer Ratio	Current Gain Group A h_{re}	—	$1.5 \cdot 10^{-4}$	—	—
	B h_{re}	—	$2 \cdot 10^{-4}$	—	—
	C h_{re}	—	$3 \cdot 10^{-4}$	—	—
DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ }\mu A$					
	Current Gain Group A h_{FE}	—	90	—	—
	B h_{FE}	—	150	—	—
	C h_{FE}	—	270	—	—
at $-V_{CE} = 5\text{ V}$, $-I_C = 2\text{ mA}$					
	Current Gain Group A h_{FE}	110	180	220	—
	B h_{FE}	200	290	450	—
	C h_{FE}	420	520	800	—
Thermal Resistance Junction to Substrate Backside	R_{thSB}	—	—	320 ¹⁾	K/W
Thermal Resistance Junction to Ambient Air	R_{thJA}	—	—	450 ¹⁾	K/W
Collector Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 0.5\text{ mA}$ at $-I_C = 100\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{CEsat}$	—	90	300	mV
	$-V_{CEsat}$	—	250	650	mV
Base Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 0.5\text{ mA}$ at $-I_C = 100\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{BEsat}$	—	700	—	mV
	$-V_{BEsat}$	—	900	—	mV
Base-Emitter Voltage at $-V_{CE} = 5\text{ V}$, $-I_C = 2\text{ mA}$ at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	$-V_{BE}$	600	660	750	mV
	$-V_{BE}$	—	—	800	mV
Collector-Emitter Cutoff Current at $-V_{CE} = 80\text{ V}$ at $-V_{CE} = 50\text{ V}$ at $-V_{CE} = 30\text{ V}$ at $-V_{CE} = 80\text{ V}$, $T_j = 125\text{ }^\circ C$ at $-V_{CE} = 50\text{ V}$, $T_j = 125\text{ }^\circ C$ at $-V_{CE} = 30\text{ V}$, $T_j = 125\text{ }^\circ C$ at $-V_{CB} = 30\text{ V}$ at $-V_{CB} = 30\text{ V}$, $T_j = 150\text{ }^\circ C$	BC856 $-I_{CES}$	—	0.2	15	nA
	BC857 $-I_{CES}$	—	0.2	15	nA
	BC858, BC859 $-I_{CES}$	—	0.2	15	nA
	BC856 $-I_{CES}$	—	—	4	μA
	BC857 $-I_{CES}$	—	—	4	μA
	BC858, BC859 $-I_{CES}$	—	—	4	μA
	$-I_{CBO}$	—	—	15	nA
	$-I_{CBO}$	—	—	5	μA
	$-I_{CBO}$	—	—	—	μA
Gain-Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	—	150	—	MHz

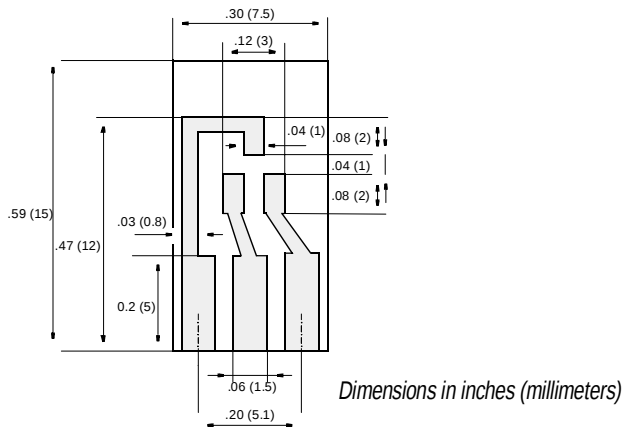
¹⁾ Device on fiberglass substrate, see layout

BC856 THRU BC859

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Typ.	Max.	Unit
Collector-Base Capacitance at $-V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{CBO}	—	—	6	pF
Noise Figure at $-V_{CE} = 5 \text{ V}$, $-I_C = 200 \mu\text{A}$, $R_G = 2 \text{ k}\Omega$, $f = 1 \text{ kHz}$, $\Delta f = 200 \text{ Hz}$ BC856, BC857, BC858	F	—	2	10	dB
BC859	F	—	1	4	dB
Noise Figure at $-V_{CE} = 5 \text{ V}$, $-I_C = 200 \mu\text{A}$, $R_G = 2 \text{ k}\Omega$, $f = 30 \dots 15000 \text{ Hz}$ BC859	F	—	1.2	4	dB



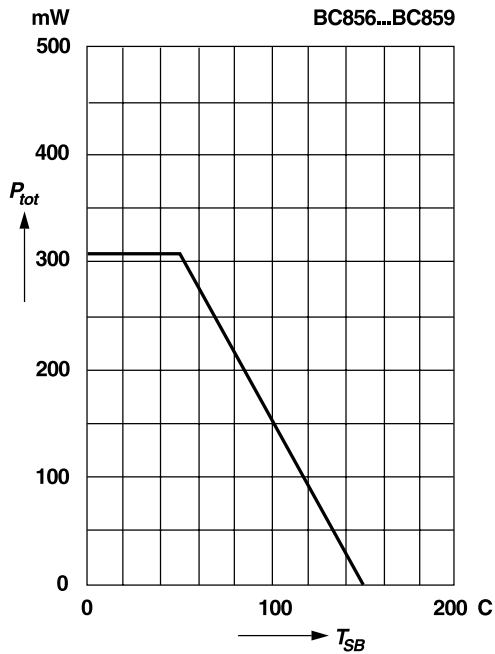
Layout for R_{thJA} test

Thickness: Fiberglass 0.059 in (1.5 mm)

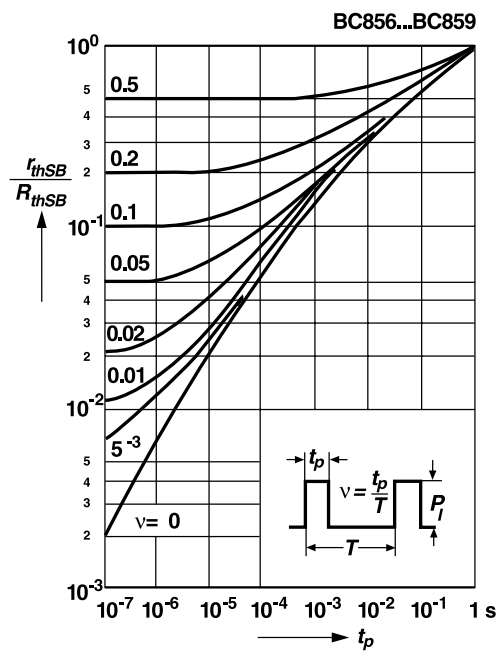
Copper leads 0.012 in (0.3 mm)

RATINGS AND CHARACTERISTIC CURVES BC856 THRU BC859

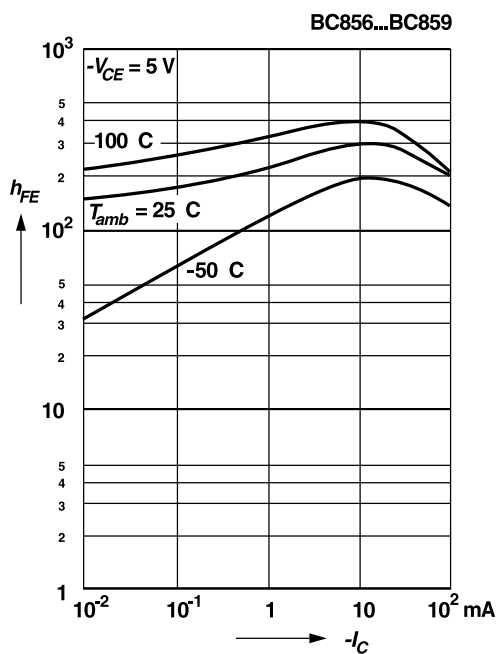
**Admissible power dissipation
versus temperature of substrate backside**
Device on fiberglass substrate, see layout



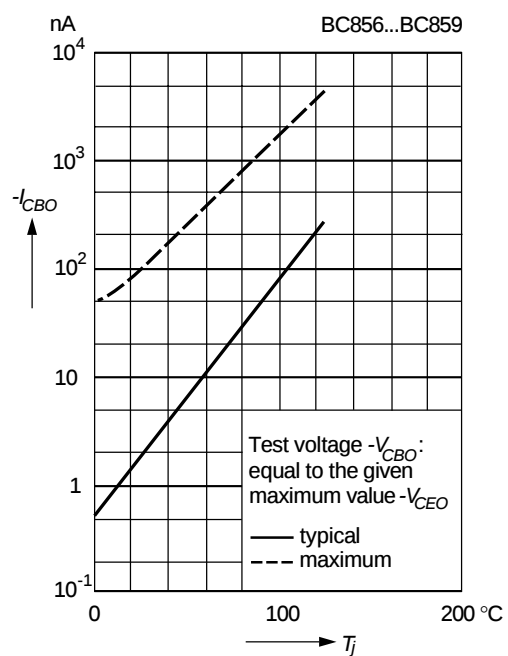
**Pulse thermal resistance
versus pulse duration (normalized)**
Device on fiberglass substrate, see layout



**DC current gain
versus collector current**

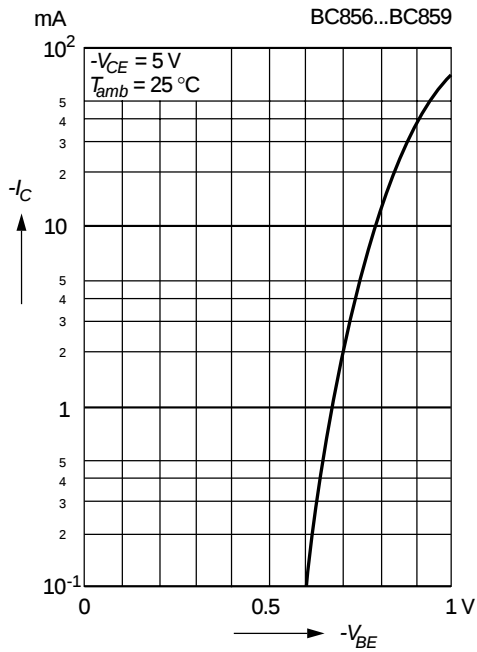


**Collector-base cutoff current
versus junction temperature**

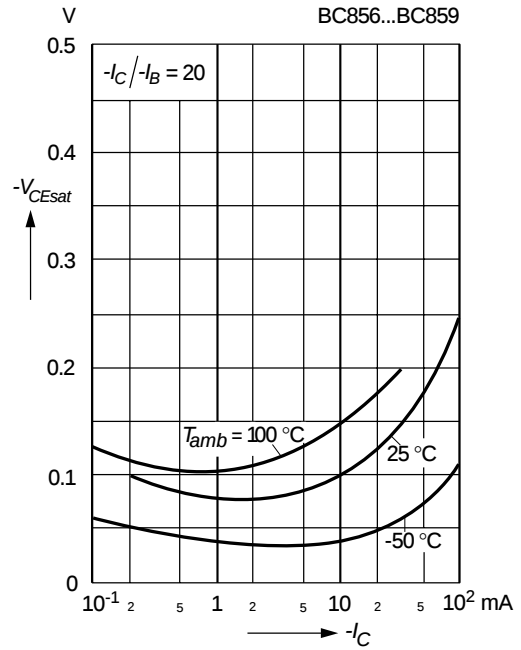


RATINGS AND CHARACTERISTIC CURVES BC856 THRU BC859

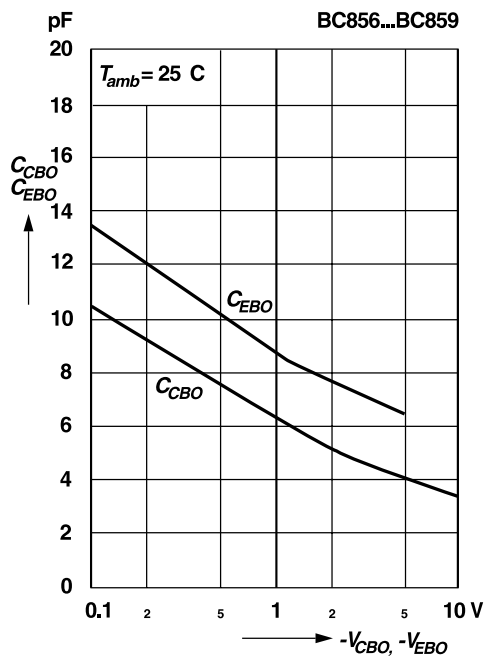
Collector current
versus base-emitter voltage



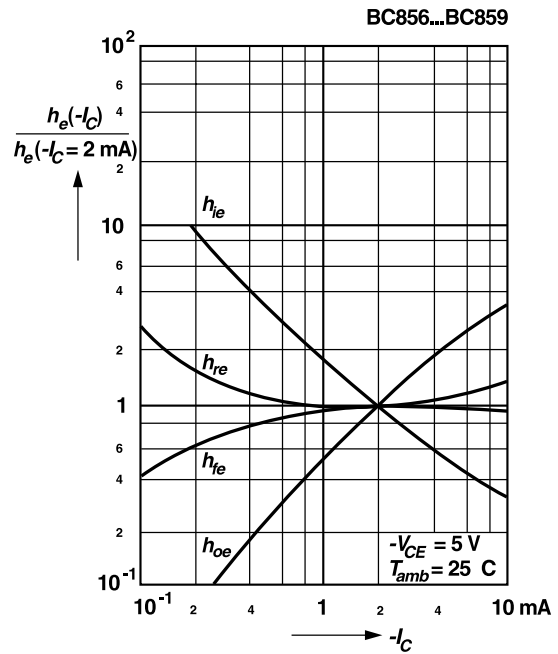
Collector saturation voltage
versus collector current



Collector-base capacitance,
Emitter-base capacitance
versus reverse bias voltage

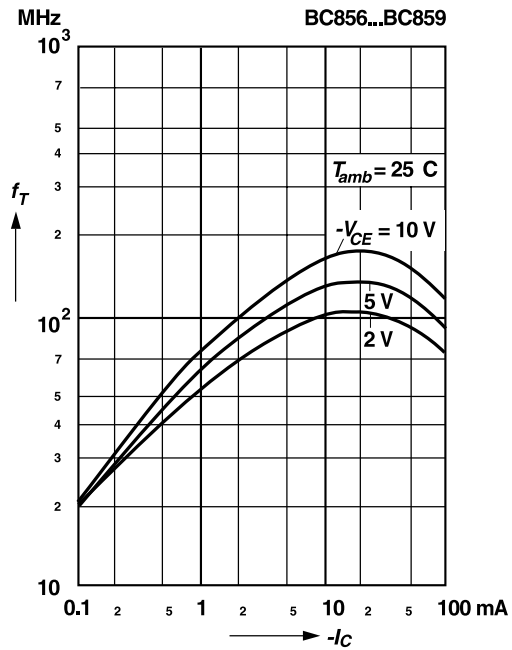


Relative h-parameters
versus collector current

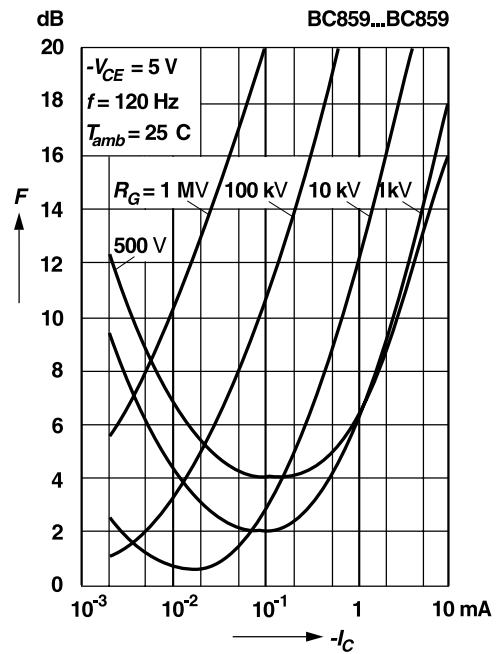


RATINGS AND CHARACTERISTIC CURVES BC856 THRU BC859

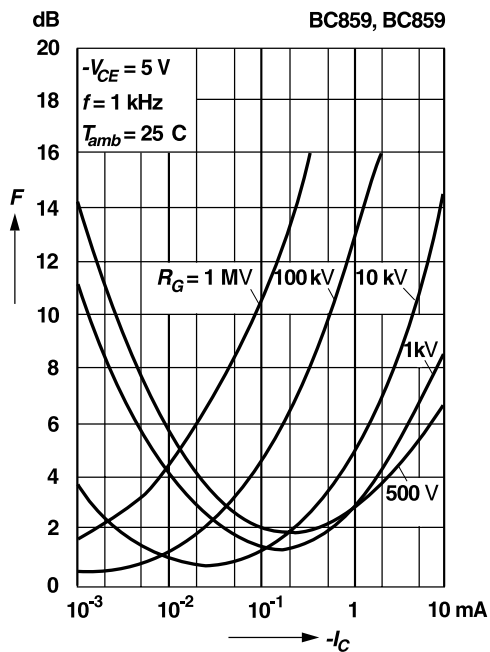
Gain-bandwidth product
versus collector current



Noise figure
versus collector current



Noise figure
versus collector current



Noise figure
versus collector-emitter voltage

